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\$/N 09/652,430

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Biswajit Sur et al.

Examiner: Andy Huynh

Serial No.:

09/652,430

Group Art Unit; 2818

Filed:

August 31, 2000

Docket No.: 884.319US1

Title:

ELECTRONIC ASSEMBLY COMPRISING SOLDERABLE THERMAL

INTERFACE (As Amended)

Customer No: 21186

Assignee: Intel Corporation

### DECLARATION UNDER 37 C.F.R. § 1.131

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

This declaration is submitted under 37 C.F.R. §1.131 prior to any final rejection of U. S. Patent Application Serial Number 09/652,430 to establish invention of the subject matter of the rejected claims prior to September 30, 1999.

- I, Biswajit Sur, do hereby declare;
- I have been employed by Intel Corporation from prior to September 30, 1999 until the l. present. My current job title is Manager of Assembly and Packaging.
- 2. I am a co-inventor of the inventive subject matter of the present application as described illustrated, and claimed therein.
- 3. Prior to September 30, 1999, the inventive subject matter that is described, illustrated, and claimed in corresponding claims of the present application was completed in the United States as evidenced by the following:
  - Prior to September 30, 1999, having earlier conceived the claimed subject matter in the United States with the co-inventors, I personally generated an Invention Disclosure, a copy of which is attached bereto as Exhibit A (7 pages). The "Invention Date" deleted from page 1 of Exhibit A is prior to September 30, 1999. Other sensitive information has been blocked out from Exhibit A.

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DECLARATION UNDER 37 C.F.R. § 1.131 Serial Number: 09/652,430 Filing Date: August 31, 2000

Paj ( ); Dbj: 884,319US1 (INT1 )

Title: ELECTRONIC ASSEMBLY COMPRISING SOLDERABLE THERMAL INTERPACE (As Amended)

- b. Figure 1 of Exhibit A illustrates conceptually an integrated circuit die attached to an organic land grid array (OLGA) substrate with solder bumps. An integrated heat spreader (IHS) is attached to the back side of the die using a low melting point solder-based thermally conductive interface material, also referred to variously in Exhibit A as "thermal interface material", a "thermal attach", and a "thermal interface".
- c. Prior to September 30, 1999, I was personally involved in the construction of prototype integrated circuit packages utilizing a solder thermal interface technique, as described in Exhibit A. My responsibilities included the design, selection, and procurement of low melting point solder materials/alloys; plating of solderable metal layers on lids; defining a suitable and manufacturable process to form a reliable thermal interface between the integrated circuit device and the lid compatible with the package and circuitry; building and testing of prototypes; and analyzing the results.
- d. The results of four different low melting point solder alloys tested are shown in Table 2 of Exhibit A. These solder alloys (Cu\_2, Cu\_281, Cu\_290, and Cu\_4) correspond to the four solder alloys identified by the corresponding Indalloy numbers in Table 1 on page 9 of the present application.
- e. Prior to September 30, 1999, I generated a Powerpoint presentation entitled "Results from Experiments on Solder Alloy as Thermal Interface Material", which summarizes the results of experiments using a low melting point solder alloy as a thermally conductive interface material. Pages 1-4 of this Powerpoint file are attached hereto as Exhibit B (4 pages). The date deleted from the footer of Exhibit B is prior to September 30, 1999. Other sensitive information has been blocked out from Exhibit B.
- f. Exhibit B. page 2, describes forming successive layers of titanium (Ti), nickel-vanadium (Ni/V), and gold (Au) on the backside of a die; coating two different types of heat spreaders, one made of aluminum-silicon-carbide (AIS:C) and the other made of

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DECLARATION UNDER 37 C FR. § 1.131 Serial Number: 09/652,430

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Filing Date: August 31, 2000
Tital: ELECTRONIC ASSEMBLY COMPRISING SOLDERABLE THERMAL INTERFACE (As Amended)
Assignee: Salet Corporation

copper (Cu), with nickel (Ni); and testing four different low melting point solder materials identified by Indalloy Numbers 281, 290, 2, and 4. Again, these solder alloys correspond to the four solder alloys identified by corresponding Indalloy numbers in Table 1 on page 9 of the present application, and they also correspond to the four solder alloys appearing in Table 2 of Exhibit A.

- Exhibit B, page 3, describes various assembly details in forming prototype g. integrated circuit packages incorporating a low melting point solder alloy as a thermally conductive interface material.
- Exhibit B, page 4, illustrates a graph of thermal resistance measurements for eig: h. different prototype integrated circuit packages incorporating a low melting point solder alloy as a thermally conductive interface material.
- When I firstshed testing and evaluating the prototype integrated circuit packages believed that they worked satisfactorily for their intended purpose, i.e. to transfer heat from an integrated circuit through a low melting point solder-based thermal interface material to a lid or integrated heat spreader.
- 4. I further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true, and further that these statements are made with the knowledge that willful false statements and the like are punishabl? by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of this application or any patent issuing thereon.

Biswajit Sur

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PAGE 05

Page Die: 684.319US1 (DIT) DECLARATION UNDER 37 C.E.R. \$ 1.131 Serial Number 09/632,430
Filing Date: August 3), 1000
Title: ELECTRONIC ASSEMBLY COMPRISING SOLDERABLE THERMAL INTERPACE (As Annobad) Assignee, Intel Corporation

BISWAJIT SUR ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. Attorneys for Intel Corporation

Walter W. Nielsen Reg. No. 25,539

CERTIFICATE UNDER 30 CPR 1.5; The undersigned hereby certifies that this correspondence is being deposited with the United States Posts Service with sufficient postage as first class read, in an envelope addressed for Commissioner of Patents, P.O. Box 1450, Alexandria, VA 223 1450, on this \_\_\_\_\_\_\_ day of September 2003.

Signature /broc

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## THE THE CONTRACTOR IS THE

### INVENTION DISCLOSURE, Rev 1 Located at: http://legal.intel.com

Fill out the below and follow the instructions:

1. Maid of the invention:

Semiconductor Process: device and integration Semiconductor Process + Equipment: thin films Semiconductor Process + Equipment: etch/litho Circuit Design

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PATENT DATABASE OROUP INTEL LEGAL TEAM

2. Concles Title of invention:

A low-mailing soft solder thermal interface technique for organic file-chip packages to dissipate a high power density.

3. Brief Description of invention (please true priv apece provided and font #10 or larger. Write the Key Elements of the Invention):

The invention is: Technique of forming a high performance thermal interface using a low-melting soft solder alloy between the Ripped die and the integrated heat aprender in an organic fip-chip package (also known as C4 OLGA). The proposed thermal interface will have a capability of dissipating a large power density. Quantizatively, this interface will provide a thermal resistance that is (at least) takes as good as compared to the best available polyments thermal interface of today. The added advantage of this specific low-melting soft animal approach is that it is not expected to negatively degrade the package reliability.

### Descriptions

Problem: Today's beet available polymeric thermal interface materials (aliver filled or sluminum filled) are capable of delivering a normalized thermal resistance of 0.4°C-cm²/W for a large die, and a target of 0.30°C-cm²/W is considered to be a stretch goal.

solutions: In order to break the thermal restrance burrier a high performance thermal interface is required. An inherent high thermal conductivity, and a proper bondline control are the two elements in achieving such a high performance interface. Using the proposed technique of this disclosure a low melting point soft solder alloy of high thermal opactuativity can be used as the thermal treatess. The proper achieving and tending control of the interface are be achieved by a proper selection of solderable interface, and process conditions.

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PAGE 07

### TIAN TOPS OF COTANGES TO THE TANK

4. Inventor(s):

Name:

Blownjit Bur Phone:

406-765-2736 Ottomship: India Group Name: PD Division Name: ATD\_

PTD\_\_\_CTM\_\_\_CR\_\_\_ STTD\_\_\_OQN\_ TCAD\_\_\_ BUTD Other?\_\_MPG

Mime: Negech Vodrahali

Phone: 480-554-5601 Citizanahip: USA

Group Name: TMG Division Name: ATD ETTO\_CON\_

SMITD\_\_\_TCAD\_\_\_ Other?\_\_\_

Jest Workman

Phoma: (408) 653-6051 Citizenanip:

USA Group Name: <u>01 moiest</u> Division Nerrus; ATO\_\_\_\_ PTD\_\_CIM\_X\_CR\_\_ STTD\_\_OQN\_\_

SMTD\_ \_\_TOAD\_\_\_ OH-T\_

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Fax

400-053-0003 Supervisor Name: Kevin J. Haley **BUM Presenter:** Steve Smith

688

Fac

Fee:

480-552-4001

Rama Shukta

BUM Presenter;

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Jim Hendribe

**Supervisor Name:** 

BUM Presenter; Ed So

Supervisor Phone: 408-785-4062 Inventor Signature:

Errepl.●

Supervisor Phone; 406-765-0319 Inventor Eignature;

Supervisor M/S: RN2-85

M/S

M/A:

CH5-185

Supervisor M/R:

BC12-504

SC12-504

Empl.

e

Supervisor Phone: (408) 786-9890 Inventor Signature: Supervisor M/3:

MS

RN2-35

RN2-35

### (PROVIDE SAME INFORMATION AS ABOVE FOR EACH ADDITIONAL INVENTOR)

HAVE YOUR SUPERVISOR READ, DATE AND SIGN COMPLETED FORM (use first inventor's 5. supervisor if, multiple, inventors)

DATE:

SUPERVISOR NAME:

BY THIS SIGNING, I (SUPERVISOR) ACKNOWLEDGE THAT I HAVE READ AND UNDERSTAND THE DISCLOSURE, AND RECOMMEND THAT THE HONORARIUM BE PAID.

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PAGE 09

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PAGE 09

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PAGE 10

### THE ROLL COLLEGE AND REAL REPORTS

- Hes subject metter of present disclosure been disclosed or will it be disclosed outside intel?

  Wees, explain and give date:

  No. But outsides can determine the technique by cross-sectioning e peckage. The surflest implementation of this technique in a package can be (Give expected tape out data if applicable):
- Has the subject matter of present disclosure been published or will it be published outside of Not planned currently. Intel? If yes, explain and give date:
- Here a product using or manufactured using the present disclosure been sold or offered for sale? If you, explain and give date: If auccessful, will be used in future products. Earliest
- Has this invention been conceived, or constructed during accomplishment of a government or third party contract? If you, give contract name and number:
- 10. Explain the problem being addressed by the invention:

This invention addresses the problem of:

Today's best available polymeric thermal interlace materials (aliver filled or sluminum filled) are capable of delivering a normalized thermal resistance of 0,4°C-cm²AV for a terms die.

Moreover, many polymeric meterials also produce inherent process artifacts, such as, reain separation, out-pensing, spreader to dis delamination, pump-out, etc.

11. Explain surrent state of the art (Le, how the problem is acreed today):

Presently the problem described above is enhad by:

A stretch goal of 0.3°C-cm<sup>2</sup>W is anticipated today using a polyment material as thermal interlace of a large die, and any further improvement is essured not activisable.

12. Explain technical advantages of the invention over ourrent state of the art.

The technical advantage of this invention is:

The proposed utilization of a highly conductive solder alloy will provide a thermal resistance that is (at least) twice as good as compared to the best available polymeric thermal interface of today. Moreover, the utilization of a cost scaler is to keep peckage and die level stresses low. The choice of a low-melting point is to attain a relatively lower processing temperature and thereby reducing warpage induced stress in the system. The above two conditions are intended to reduce total stress level in an OLGA2 peckage and thereby enhance the package reliability.

13. a. Is the invention experimentally verified?

Yee.

b. In the invention verified with simulation?

No. c. If neither a. or b. above, then you can get a patent on the concept, but plants expiain the technical beels to justify that your invention will work (use extra space if necessary):

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14. Detailed Description of Invention (try to take only the enture provided with fort #10 or larger type.

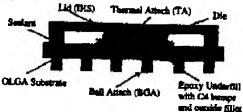


Figure 1. Schematic of an OLGA2 package showing the buckside of the attached to 1825 with the help of thermal interface material.

As a beckground, on OLGA2 package consists of a filp-chip silicon dis attached to an organic land grid array (OLGA) substrate with the help of C4 bumps and an underfill epoxy. An integrated heat apreader (IHSI) is attached to the backside of the filp-chip die for heat dissipation. A thermaly conductive integrated (which is the topic of this discionure) is used to attach the IHS to the disc. IHS is also attached to the substrate boundary with the help of a sealant for mechanical support. Various components of an OLGA2 package, including the thermal interface / thermal attach are schematically shown in Figure 1.

For forming a low-melting eofs eolder thermal interface the following four components are essential: 1) a solderable die backside, 2) a solderable BHS, 3) a suitable solder pasts, and 4) a suitable process for forming a reliable interface. A procedure for echieving the above four is described in the following.

- 1) Firstly metal layers are required to be deposited on the backside of die (unpolished water) for solderability. The backside of an unpolished water is prepared with a 10 accord aputter eith before the metal deposition/sputtering. The metal layer build-up is as follows: a 600Å layer of Ti on backside of the die, followed by a 3500Å layer of NIV, and finally a 600Å layer of Au. The sputtering parameters are almitten to that used for POPI C4 BLM processing (C4 BLM TI, C4 BLM NIV), with the addition a gold layer with a P6 backside Au-parameters (except for shorter deposition time). Test waters of 2C112M45 device were used for this test.
- 2) Solderability on IHS can be achieved with a presence of a suitable metal. Two types of IHS materials (Cu and ASIC) were tried in this locability test. A 2 to 5 µm thick Ni layer with shiny finish was lound suitable for attaining solderability on both the material types. Electroless Ni pleting was done in a Niklad 787 bath, using a medium force solution.
- 3) Several different solder alloys (\$\text{Bit}\$ or in alloy) were tried out and found suitable for this thermal interface application. All of them were off-the-shelf materials from indultoy Corp, and were available in solder pasts form. The solder pasts consists of a no-clean flux vehicle and a 89% loading of the corresponding solder alloy. The solder compositions and relevant properties are given in the following Table 1.

Table 1. Comparitions and relevant properties of the solder alloys used in this experiment.

Indelicy Number	Composition	Liquidus	Soldae (*C)	Thermal Conductivity (Miny C)
281	53 EI / 40 Pm	188	136	
296	97.95/3An	143	143	73
	H 14/15 Ph/8As	154	140	44
4	100 in	1/17		

4) During assembly process the solder pasts is first applied at backgide of die, and then the peakent meterial is dispensed on the peakent boundary. The IHS is then placed, and IHS spring is attached to apply a 3 to 5 lbs of force. The units in a FOL carrier are then reliowed in N2 environment inside a horizontal BTU furnace for forming the solder joints. During reflow operation of each alloy, the maximum zone temperature in the furnace was maintained as fliguidus + 30°C' and the time above liquidus was -60 accs. Poet solder join the sealant was cured in a conventional vertical even.

Drawings (use as marry pages as meaded) (PLEASE DO NOT MAKE COLOR DRAWINGS)

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### HATER COMBINED FIRE

16. Key Supporting Date (1 page limit on separate page):

The experimental teasibility of this technique is shown in the following figures. The thermal resistance data from 4 alloys were referred to by their numbers and by the type of apreadate (for example, Cu\_2 means Cu apreadar with indelloys?) combination). Only the data for Cu BHS is demonstrated here.

Figure 2. Comparison of thermal interface resistance (\*C-cm²/W) between all the alloys tested and the present plan of record material. Data shown are for the center sensor (RTD3) for a 2C11ZL die (884:204 mile)

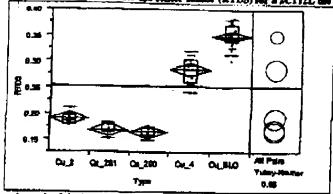
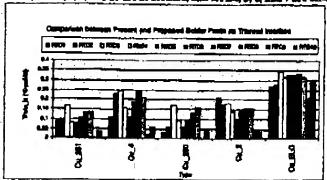


Table 2. Mean and standard deviations of therstal resistance at the conter for all legs tested.

libers and 8	M Day letters			
Levi	Humber	Man	and Day	Std Mr Man
2بت	7	0.140	0.011	0.004
{ Cu_201	,	0.166	9.910	0.004
Cor⊤saco	7	0.186	0.00	0.003
CU_4	7	0.285	Ö.035	0.010
(O)_#TD	45	0.549	0.022	0.008

Figure 3. Therand resistance for all the temperature scanors for all the lags (only 1 unit per lag shown). RTD3 and 8 are at center, RTD1, 2, 2, and 10 are at corners, and RTD4, 5, 6, and 7 are off-ountered in the dis.



From above figures and table it is clear that the proposed solder thermal interface technique outperformed the present POR interface, both statistically and technically, by a vast margin (Fig. 1 and Table 2). This improvement is noticed uniformly all across the cite, we can be seen for all the sensors (Fig. 3). It is to be also noted that, without any process optimization, this proof of concept test already showed about a 2x improvement in thermal performance.

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EXHIBIT B - Page 1

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Results from Experiment on Solder Alloy as Thermal Interface Material

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PAGE

## **Build Details**

- 2C112L device was used for this investigation
- Metal was sputtered on backside of die (wafer) for solderability
  - Wafers did not have any backside polishing step
- Metal sputtering on backside at D2: 500Å Ti + 3500Å NiN + 600Å Au

AlSiC (CPS) spreaders were coated with

Ni plating (electroless) at a Santa Clara shop

Cu (Shinko) spreaders had POR Ni coating

Four (4) 'off-the-shelf solder pastes used as thermal interface material

							_
of America	Thermal Conductivity	(W/m-°C)	19	73	43	86	
poration	Solidus	(၁)	138	143	149	₽	
Solder paste supplier: Indium Corporation of America	Liquidus	၌	138	143	154	157	
	Composition		58 Bi / 42 Sn	97 In / 3 Ag	80 In / 15 Pb /	100 In	
Solder paste	Indelioy Number Composition		281	290	2	4	
1							

EXHIBIT B - Page 2

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# **Build Details (Contd.)**

IHS Assembly Details:

1) Solder paste manually applied at backside of die

2) Sealant dispensed on package

3) Spreader placed using manual SPM and template

4) IHS springs attached

IHS spring used:

5) Reflowed in chip-join BTU furnace for solder joint of thermal interface

Belt speed:

Temperatures:

Environment: 6) Cured

EXHIBIT B - Page 3

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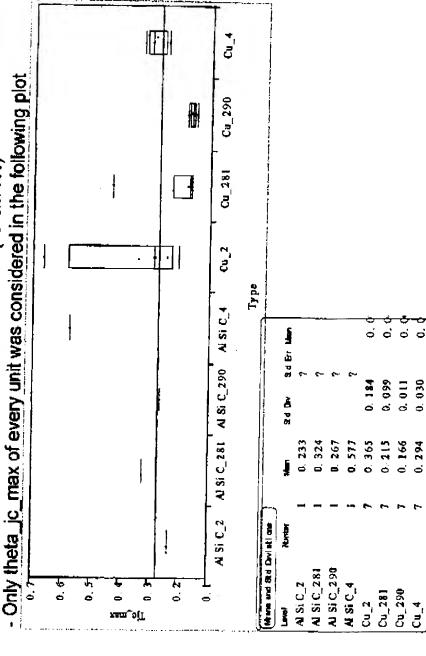
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Thermal resistance is normalized for die area (\*C-cm²/W)



thermal resistance. For example:  $(lot_\mu + 3*lot_\sigma)$  for  $(Cu+Alloy290) = 0.199 °C-cm^2/W$ - Results show proof-of-concept that 'solder' thermal interface can give a very low

Summary

EXHIBIT B - Page 4

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